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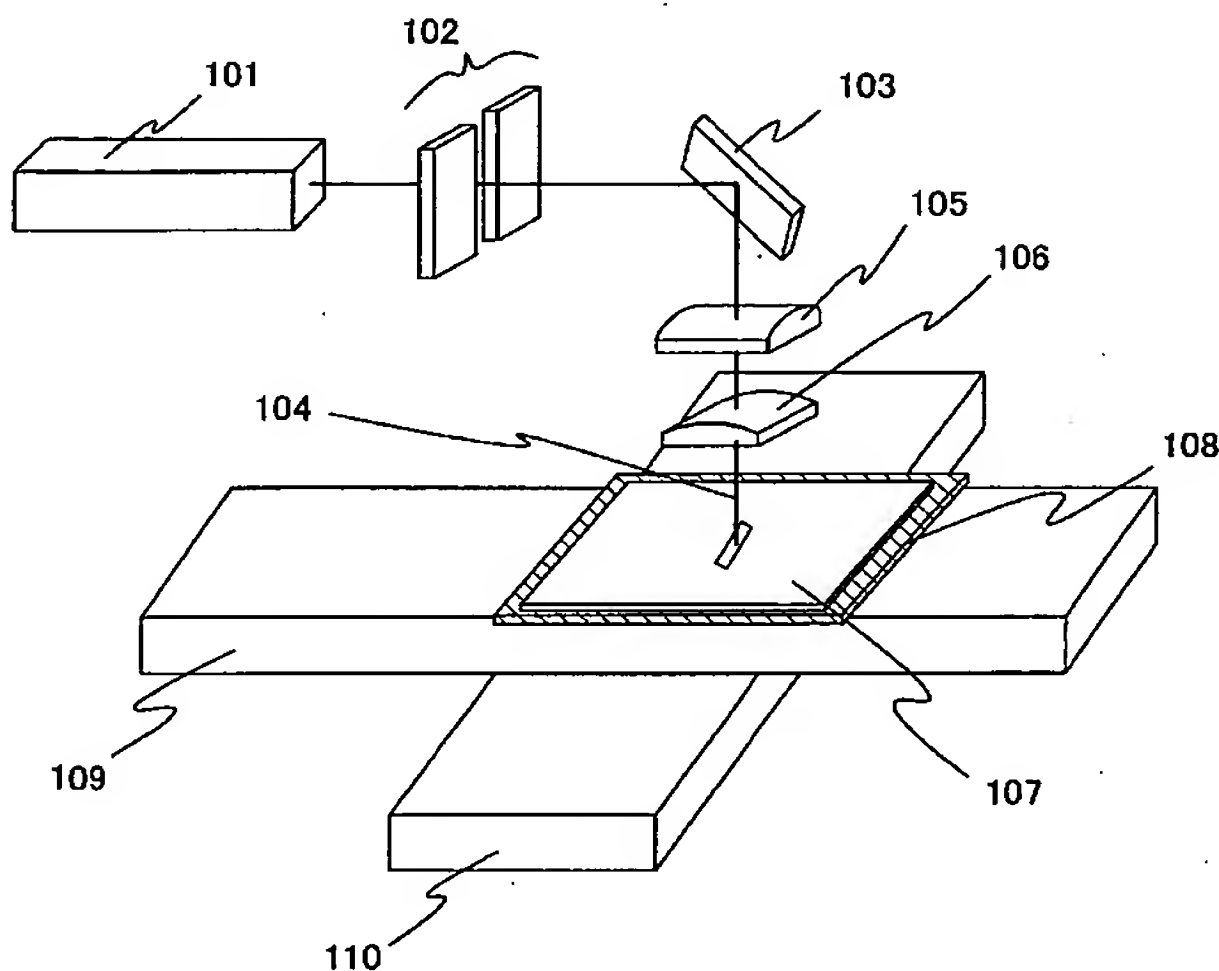
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(54) Title: SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD



(57) Abstract: It is an object of the present invention to provide laser irradiation apparatus and method which can decrease the proportion of the microcrystal region in the whole irradiated region and can irradiate a semiconductor film homogeneously with a laser beam. A low-intensity part of a laser beam emitted from a laser oscillator is blocked by a slit, the laser beam is deflected by a mirror, and the beam is shaped into a desired size by using two convex cylindrical lenses. Then, the laser beam is delivered to the irradiation surface.

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